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Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I ² C, IrDA, LINbus, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, POR, PWM, WDT
Number of I/O	15
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	1K x 8
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 10x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	20-TSSOP (0.173", 4.40mm Width)
Supplier Device Package	20-TSSOP
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l031f6p6

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

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2 Description

The access line ultra-low-power STM32L031x4/6 family incorporates the high-performance ARM[®] Cortex[®]-M0+ 32-bit RISC core operating at a 32 MHz frequency, high-speed embedded memories (up to 32 Kbytes of Flash program memory, 1 Kbytes of data EEPROM and 8 Kbytes of RAM) plus an extensive range of enhanced I/Os and peripherals.

The STM32L031x4/6 devices provide high power efficiency for a wide range of performance. It is achieved with a large choice of internal and external clock sources, an internal voltage adaptation and several low-power modes.

The STM32L031x4/6 devices offer several analog features, one 12-bit ADC with hardware oversampling, two ultra-low-power comparators, several timers, one low-power timer (LPTIM), three general-purpose 16-bit timers, one RTC and one SysTick which can be used as timebases. They also feature two watchdogs, one watchdog with independent clock and window capability and one window watchdog based on bus clock.

Moreover, the STM32L031x4/6 devices embed standard and advanced communication interfaces: one I2C, one SPI, one USART, and a low-power UART (LPUART).

The STM32L031x4/6 also include a real-time clock and a set of backup registers that remain powered in Standby mode.

The ultra-low-power STM32L031x4/6 devices operate from a 1.8 to 3.6 V power supply (down to 1.65 V at power down) with BOR and from a 1.65 to 3.6 V power supply without BOR option. They are available in the -40 to +125 °C temperature range. A comprehensive set of power-saving modes allows the design of low-power applications.







Operating power supply	Functionalities depending on the operating power supply range					
range	ADC operation Dynamic voltage scaling range		I/O operation			
V _{DD} = 1.65 to 1.71 V	Conversion time up to 570 ksps	Range 2 or range 3	Degraded speed performance			
V _{DD} = 1.71 to 2.0 V ⁽¹⁾	Conversion time up to 1.14 Msps	Range 1, range 2 or range 3	Degraded speed performance			
V _{DD} = 2.0 to 2.4 V	Conversion time up to 1.14 Msps	Range 1, range 2 or range 3	Full speed operation			
V _{DD} = 2.4 to 3.6 V	Conversion time up to 1.14 Msps	Range 1, range 2 or range 3	Full speed operation			

 CPU frequency changes from initial to final must respect the condition: f_{CPU initial} <4f_{CPU initial}. It must also respect 5 µs delay between two changes. For example to switch from 4.2 MHz to 32 MHz, you can switch from 4.2 MHz to 16 MHz, wait 5 µs, then switch from 16 MHz to 32 MHz.

Tuble i e l'equelle i unge depending en dyname verage eeung

CPU frequency range	Dynamic voltage scaling range
16 MHz to 32 MHz (1ws) 32 kHz to 16 MHz (0ws)	Range 1
8 MHz to 16 MHz (1ws) 32 kHz to 8 MHz (0ws)	Range 2
32 kHz to 4.2 MHz (0ws)	Range 3

Table 5. Functionalities depending on the working mode(from Run/active down to standby) ⁽¹⁾

			Low-	Low-		Stop	5	Standby
IPs	Run/Active	Sleep	power run	power sleep		Wakeup capability		Wakeup capability
CPU	Y		Y					
Flash memory	0	0	0	0				
RAM	Y	Y	Y	Y	Y			
Backup registers	Y	Y	Y	Y	Y		Y	
EEPROM	0	0	0	0				
Brown-out reset (BOR)	0	О	0	0	0	0	0	0
DMA	0	0	0	0				
Programmable Voltage Detector (PVD)	0	0	0	0	0	0	-	



3.6 Low-power real-time clock and backup registers

The real time clock (RTC) and the 5 backup registers are supplied in all modes including standby mode. The backup registers are five 32-bit registers used to store 20 bytes of user application data. They are not reset by a system reset, or when the device wakes up from Standby mode.

The RTC is an independent BCD timer/counter. Its main features are the following:

- Calendar with subsecond, seconds, minutes, hours (12 or 24 format), week day, date, month, year, in BCD (binary-coded decimal) format
- Automatically correction for 28, 29 (leap year), 30, and 31 day of the month
- Two programmable alarms with wake up from Stop and Standby mode capability
- Periodic wakeup from Stop and Standby with programmable resolution and period
- On-the-fly correction from 1 to 32767 RTC clock pulses. This can be used to synchronize it with a master clock.
- Reference clock detection: a more precise second source clock (50 or 60 Hz) can be used to enhance the calendar precision.
- Digital calibration circuit with 1 ppm resolution, to compensate for quartz crystal inaccuracy
- 2 anti-tamper detection pins with programmable filter. The MCU can be woken up from Stop and Standby modes on tamper event detection.
- Timestamp feature which can be used to save the calendar content. This function can be triggered by an event on the timestamp pin, or by a tamper event. The MCU can be woken up from Stop and Standby modes on timestamp event detection.

The RTC clock sources can be:

- A 32.768 kHz external crystal
- A resonator or oscillator
- The internal low-power RC oscillator (typical frequency of 37 kHz)
- The high-speed external clock

3.7 General-purpose inputs/outputs (GPIOs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions, and can be individually remapped using dedicated alternate function registers. All GPIOs are high current capable. Each GPIO output, speed can be slowed (40 MHz, 10 MHz, 2 MHz, 400 kHz). The alternate function configuration of I/Os can be locked if needed following a specific sequence in order to avoid spurious writing to the I/O registers. The I/O controller is connected to a dedicated IO bus with a toggling speed of up to 32 MHz.

Extended interrupt/event controller (EXTI)

The extended interrupt/event controller consists of 26 edge detector lines used to generate interrupt/event requests. Each line can be individually configured to select the trigger event (rising edge, falling edge, both) and can be masked independently. A pending register maintains the status of the interrupt requests. The EXTI can detect an external line with a pulse width shorter than the Internal APB2 clock period. Up to 38 GPIOs can be connected to the 16 configurable interrupt/event lines. The 10 other lines are connected to PVD, RTC, USART, I2C, LPUART, LPTIMER or comparator events.



3.12 Ultra-low-power comparators and reference voltage

The STM32L031x4/6 embed two comparators sharing the same current bias and reference voltage. The reference voltage can be internal or external (coming from an I/O).

- One comparator with ultra low consumption
- One comparator with rail-to-rail inputs, fast or slow mode.
- The threshold can be one of the following:
 - External I/O pins
 - Internal reference voltage (V_{REFINT})
 - submultiple of Internal reference voltage(1/4, 1/2, 3/4) for the rail to rail comparator.

Both comparators can wake up the devices from Stop mode, and be combined into a window comparator.

The internal reference voltage is available externally via a low-power / low-current output buffer (driving current capability of 1 μ A typical).

3.13 System configuration controller

The system configuration controller provides the capability to remap some alternate functions on different I/O ports.

The highly flexible routing interface allows the application firmware to control the routing of different I/Os to the TIM2, TIM21, TIM22 and LPTIM timer input captures. It also controls the routing of internal analog signals to the ADC, COMP1 and COMP2 and the internal reference voltage V_{REFINT} .

3.14 Timers and watchdogs

The ultra-low-power STM32L031x4/6 devices include three general-purpose timers, one low- power timer (LPTM), two watchdog timers and the SysTick timer.

Table 9 compares the features of the general-purpose and basic timers.

Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/compare channels	Complementary outputs
TIM2	16-bit	Up, down, up/down	Any integer between 1 and 65536	Yes	4	No
TIM21, TIM22	16-bit	Up, down, up/down	Any integer between 1 and 65536	No	2	No

 Table 9. Timer feature comparison



the software during runtime, to be compared with a reference signature generated at linktime and stored at a given memory location.

3.17 Serial wire debug port (SW-DP)

An ARM SW-DP interface is provided to allow a serial wire debugging tool to be connected to the MCU.



		Pin	Num	ber								
TSSOP20	WLCSP25 ⁽¹⁾	UFQFPN28	UFQFPN28 (STM32L031GxUxS only)	LQFP32	UFQFPN32 ⁽²⁾	LQFP48	Pin name (function after reset)	Pin type	I/O structure	Note	Alternate functions	Additional functions
-	-	-	-	-	-	2	PC13- ANTI_TAMP	I/O	FT	-	-	TAMP1/WKUP2
2	B5	2	2	2	2	3	PC14- OSC32_IN	I/O	тс	-	-	OSC32_IN
3	C5	3	3	3	3	4	PC15- OSC32_OUT	I/O	тс	-	-	OSC32_OUT
-	-	-	-	-	-	5	PH0-OSC_IN	I/O	тс	-	-	-
I	-	-	-	-	-	6	PH1- OSC_OUT	I/O	тс	-	-	-
4	D5	4	4	4	4	7	NRST	I/O	I	-	-	-
-	-	-	-	-	-	1	PC0	I/O	FT	-	LPTIM1_IN1, EVENTOUT, LPUART1_RX	-
-	E1	-	-	-	"0"	8	VSSA	S	-	-	-	-
5	C4	5	5	5	5	9	VDDA	S	-	-	-	-
6	E5	6	6	6	6	-	PA0-CK_IN	I/O	тс	-	LPTIM1_IN1, TIM2_CH1, USART2_CTS, TIM2_ETR, COMP1_OUT	COMP1_INM6, ADC_IN0, RTC_TAMP2/WKUP1
-	-	-	-	-	-	10	PA0	I/O	тс	-	LPTIM1_IN1, TIM2_CH1, USART2_CTS, TIM2_ETR, COMP1_OUT	COMP1_INM6, ADC_IN0, RTC_TAMP2/WKUP1



6 Electrical characteristics

6.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS}.

6.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at $T_A = 25$ °C and $T_A = T_Amax$ (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean $\pm 3\sigma$).

6.1.2 Typical values

Unless otherwise specified, typical data are based on T_A = 25 °C, V_{DD} = 3.6 V (for the 1.65 V $\leq V_{DD} \leq$ 3.6 V voltage range). They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean $\pm 2\sigma$).

6.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

6.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in *Figure 11*.

6.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in *Figure 12*.





Symbol	Ratings	Max.	Unit	
$\Sigma I_{VDD}^{(2)}$	Total current into sum of all V_{DD} power lines (source) ⁽¹⁾	105		
ΣI _{VSS} ⁽²⁾	Total current out of sum of all V_{SS} ground lines (sink) ⁽¹⁾	105		
I _{VDD(PIN)}	Maximum current into each V _{DD} power pin (source) ⁽¹⁾	100		
I _{VSS(PIN)}	Maximum current out of each V _{SS} ground pin (sink) ⁽¹⁾			
	Output current sunk by any I/O and control pin except FTf pins			
I _{IO}	Output current sunk by FTf pins	22		
	Output current sourced by any I/O and control pin	-16		
Total output current sunk by sum of all IOs and control pins ⁽⁴⁾		45	mA	
∠iio(pin)` ′	Total output current sourced by sum of all IOs and control pins ⁽⁴⁾	-45		
ΣL ⁽⁵⁾	Total output current sunk by sum of all IOs and control pins ⁽²⁾	90		
∠IO(PIN)	Total output current sourced by sum of all IOs and control pins ⁽²⁾	-90		
I	Injected current on FT, FFf, RST and B pins	-5/+0 ⁽⁶⁾		
'INJ(PIN)	Injected current on TC pin	± 5 ⁽⁷⁾		
ΣΙ _{INJ(PIN)}	PIN) Total injected current (sum of all I/O and control pins) ⁽⁸⁾			

Table 18.	Current	characteristics
-----------	---------	-----------------

All main power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.

2. This current consumption must be correctly distributed over all I/Os and control pins. The total output current must not be sunk/sourced between two consecutive power supply pins referring to high pin count LQFP packages.

- 3. These values apply only to STM32L031GxUxS part number.
- 4. This current consumption must be correctly distributed over all I/Os and control pins. In particular, it must be located the closest possible to the couple of supply and ground, and distributed on both sides.
- 5. These values apply to all part numbers except for STM32L031GxUxS.
- 6. Positive current injection is not possible on these I/Os. A negative injection is induced by V_{IN} <V_{SS}. I_{INJ(PIN)} must never be exceeded. Refer to *Table 17* for maximum allowed input voltage values.
- A positive injection is induced by V_{IN} > V_{DD} while a negative injection is induced by V_{IN} < V_{SS}. I_{INJ(PIN)} must never be exceeded. Refer to *Table 17: Voltage characteristics* for the maximum allowed input voltage values.
- 8. When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values).

Table 19. Thermal characteristics

Symbol	Ratings	Value	Unit
T _{STG}	Storage temperature range	–65 to +150	°C
TJ	Maximum junction temperature	150	°C



Symbol	Parameter	Co	f _{HCLK}	Тур	Max ⁽¹⁾	Unit		
S I _{DD} c (Run F				1 MHz	140	200	μA	
			Range 3, V _{CORE} =1.2 V	2 MHz	245	310		
				4 MHz	460	540		
		f _{HSE} = f _{HCLK} up to		4 MHz	0.56	0.63		
		Supply urrent in Run mode, ode xecuted rom Flash	Range 2, V _{CORE} =1.5 V, VOS[1:0]=10.	8 MHz	1.1	1.2	mA	
	Supply current in Run mode, code executed from Flash			16 MHz	2.1	2.3		
			Range 1, V _{CORE} =1.8 V, VOS[1:0]=01	8 MHz	1.25	1.4		
				16 MHz	2.5	2.7		
Flash)				32 MHz	5	5.6		
			Range 2, V _{CORE} =1.5 V, VOS[1:0]=10,	16 MHz	2.1	2.4		
			Range 1, V _{CORE} =1.8 V, VOS[1:0]=01	32 MHz	5.1	5.7		
				65 kHz	34.5	110		
		MSI clock	Range 3, V _{CORE} =1.2 V, VOS[1:0]=11	524 kHz	86	150	μA	
				4.2 MHz	505	570		

Table 24. Current consumption in Run mode, code with data processing running from Flash memory

1. Guaranteed by characterization results at 125 $^\circ\text{C},$ unless otherwise specified.

2. Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

Table 25. Current consumption in Run mode vs code type,
code with data processing running from Flash memory

Symbol	Parameter	Conditions			f _{HCLK}	Тур	Unit
I _{DD} (Run from Flash) Supply current in Run mode, code executed from Flash memory				Dhrystone		460	
				CoreMark		455	
	$f_{HSE} = f_{HCLK}$ up to 16 MHz included, $f_{HSE} = f_{HCLK}/2$ above 16 MHz (PLL ON) ⁽¹⁾	Range 3, V _{CORE} =1.2 V, VOS[1:0]=11	Fibonacci	4 MHz	330	μA	
			while(1)		305		
			while(1), prefetch OFF		320		
		Range 1, VOSI1:01=01	Dhrystone		5	mA	
			CoreMark		5.15		
			Fibonacci	32 MHz	5		
			V _{CORE} =1.8 V	while(1)		4.35	
				while(1), prefetch OFF		3.85	

1. Oscillator bypassed (HSEBYP = 1 in RCC_CR register).



6.3.7 Internal clock source characteristics

The parameters given in *Table 41* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 20*.

High-speed internal 16 MHz (HSI16) RC oscillator

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{HSI16}	Frequency	V _{DD} = 3.0 V	-	16	-	MHz
(1)(2)	HSI16 user-	Trimming code is not a multiple of 16	-	±0.4	0.7	%
TRIM	trimmed resolution	Trimming code is a multiple of 16	-	-	± 1.5	%
		V _{DDA} = 3.0 V, T _A = 25 °C	-1 ⁽³⁾	-	1 ⁽³⁾	%
ACC _{HSI16} (2) Accuracy of the factory-calibrate HSI16 oscillator		V _{DDA} = 3.0 V, T _A = 0 to 55 °C		-	1.5	%
	Accuracy of the factory-calibrated HSI16 oscillator	V_{DDA} = 3.0 V, T_A = -10 to 70 °C	-2	-	2	%
		V_{DDA} = 3.0 V, T_A = -10 to 85 °C	-2.5	-	2	%
		V _{DDA} = 3.0 V, T _A = -10 to 105 °C	-4	-	2	%
		V _{DDA} = 1.65 V to 3.6 V T _A = -40 to 125 °C	-5.45	-	3.25	%
t _{SU(HSI16)} ⁽²⁾	HSI16 oscillator startup time	-	-	3.7	6	μs
I _{DD(HSI16)} ⁽²⁾	HSI16 oscillator power consumption	-	-	100	140	μA

1. The trimming step differs depending on the trimming code. It is usually negative on the codes which are multiples of 16 (0x00, 0x10, 0x20, 0x30...0xE0).

2. Guaranteed by characterization results.

3. Guaranteed by test in production.







Symbol	Parameter	Conditions	ns Min Typ Max		Мах	Unit
+ (3)	Calibration time	f _{ADC} = 16 MHz		5.2		μs
^L CAL ⁽¹⁾				83		
W _{LATENCY} ADC_DF latency		ADC clock = HSI16	1.5 ADC cycles + 2 f _{PCLK} cycles	-	1.5 ADC cycles + 3 f _{PCLK} cycles	-
	ADC_DR register write latency	ADC clock = PCLK/2	-	4.5	-	f _{PCLK} cycle
		ADC clock = PCLK/4	-	8.5	-	f _{PCLK} cycle
		$f_{ADC} = f_{PCLK}/2 = 16 \text{ MHz}$	0.266			μs
	Trigger conversion latency	$f_{ADC} = f_{PCLK}/2$	8.5			1/f _{PCLK}
t _{latr} (3)		$f_{ADC} = f_{PCLK}/4 = 8 \text{ MHz}$	0.516			μs
		$f_{ADC} = f_{PCLK}/4$	16.5			1/f _{PCLK}
		f _{ADC} = f _{HSI16} = 16 MHz	0.252	-	0.260	μs
Jitter _{ADC}	ADC jitter on trigger conversion	f _{ADC} = f _{HSI16}	-	1	-	1/f _{HSI16}
+ (3)	Sompling time	f _{ADC} = 16 MHz	0.093	-	10.03	μs
IS (1)			1.5	-	239.5	1/f _{ADC}
t _{STAB} ⁽³⁾	Power-up time		0	0	1	μs
	Total conversion time	f _{ADC} = 16 MHz	0.875		10.81	μs
t _{ConV} ⁽³⁾	(including sampling time)		14 to 173 (t _S for sampling +12.5 for successive approximation)			1/f _{ADC}

Table 57. ADC characteristics (continued)

1. V_{DDA} minimum value can be decreased in specific temperature conditions. Refer to *Table 58: RAIN max for fADC* = 16 *MHz*.

2. A current consumption proportional to the APB clock frequency has to be added (see *Table 34: Peripheral current consumption in Run or Sleep mode*).

3. Guaranteed by design.

 Standard channels have an extra protection resistance which depends on supply voltage. Refer to Table 58: RAIN max for fADC = 16 MHz.

Equation 1: $R_{AIN} max$ formula

$$R_{AIN} < \frac{r_{S}}{f_{ADC} \times C_{ADC} \times \ln(2^{N+2})} - R_{ADC}$$

The formula above (*Equation 1*) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. Here N = 12 (from 12-bit resolution).



7 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status *are available at http://www.st.com.* ECOPACK[®] is an ST trademark.

7.1 LQFP48 package information



Figure 34. LQFP48, 7 x 7 mm, 48-pin low-profile quad flat package outline

1. Drawing is not to scale.





Figure 41. UFQFPN32 recommended footprint

1. Dimensions are expressed in millimeters.

UFQFPN32 device marking

The following figure gives an example of topside marking versus pin 1 position identifier location.





Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering 1. samples to run qualification activity.

7.4 UFQFPN28 package information



Figure 43. UFQPN28, 4 x 4 mm, 28-pin package outline

1. Drawing is not to scale.

Symbol	millimeters			inches			
Symbol	Min	Тур	Мах	Min	Тур	Мах	
А	0.500	0.550	0.600	0.0197	0.0217	0.0236	
A1	-	0.000	0.050	-	0.0000	0.0020	
D	3.900	4.000	4.100	0.1535	0.1575	0.1614	
D1	2.900	3.000	3.100	0.1142	0.1181	0.1220	
E	3.900	4.000	4.100	0.1535	0.1575	0.1614	
E1	2.900	3.000	3.100	0.1142	0.1181	0.1220	
L	0.300	0.400	0.500	0.0118	0.0157	0.0197	
L1	0.250	0.350	0.450	0.0098	0.0138	0.0177	
Т	-	0.152	-	-	0.0060	-	
b	0.200	0.250	0.300	0.0079	0.0098	0.0118	
е	-	0.500	-	-	0.0197	-	

Table 73. UFQPN28, 4 x 4 mm, 28-pin package mechanical data ^v	ata ⁽¹⁾
--	--------------------

1. Values in inches are converted from mm and rounded to 4 decimal digits.





Figure 44. UFQFPN28 recommended footprint

1. Dimensions are expressed in millimeters.

UFQFPN28 device marking

The following figure gives an example of topside marking versus pin 1 position identifier location.



Figure 45. Example of UFQFPN28 marking (package top view)

 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.



7.6 TSSOP20 package information





1. Drawing is not to scale.

Table 76. TSSOP20 – 20-lead thin shrink small outline, 6.5 x 4.4 mm, 0.65 mm pitch,
package mechanical data

Symbol		millimeters		inches ⁽¹⁾			
Symbol	Min.	Тур.	Max.	Min.	Тур.	Max.	
A	-	-	1.200	-	-	0.0472	
A1	0.050	-	0.150	0.0020	-	0.0059	
A2	0.800	1.000	1.050	0.0315	0.0394	0.0413	
b	0.190	-	0.300	0.0075	-	0.0118	
С	0.090	-	0.200	0.0035	-	0.0079	
D	6.400	6.500	6.600	0.2520	0.2559	0.2598	
E	6.200	6.400	6.600	0.2441	0.2520	0.2598	
E1	4.300	4.400	4.500	0.1693	0.1732	0.1772	
е	-	0.650	-	-	0.0256	-	
L	0.450	0.600	0.750	0.0177	0.0236	0.0295	
L1	-	1.000	-	-	0.0394	-	



Table 76. TSSOP20 – 20-lead thin shrink small out	ine, 6.5 x 4.4 mm, 0.65 mm pitch,
package mechanical data (c	ontinued)

Symbol	millimeters			inches ⁽¹⁾		
	Min.	Тур.	Max.	Min.	Тур.	Max.
k	0°	-	8°	0°	-	8°
aaa	-	-	0.100	-	-	0.0039

1. Values in inches are converted from mm and rounded to four decimal digits.

Figure 50. TSSOP20 – 20-lead thin shrink small outline, 6.5 x 4.4 mm, 0.65 mm pitch, package footprint



1. Dimensions are expressed in millimeters.



7.7 Thermal characteristics

The maximum chip-junction temperature, $T_{\rm J}$ max, in degrees Celsius, may be calculated using the following equation:

 $T_J \max = T_A \max + (P_D \max \times \Theta_{JA})$

Where:

- T_A max is the maximum ambient temperature in °C,
- Θ_{JA} is the package junction-to-ambient thermal resistance, in °C/W,
- P_D max is the sum of P_{INT} max and P_{I/O} max (P_D max = P_{INT} max + P_{I/O}max),
- P_{INT} max is the product of I_{DD} and V_{DD}, expressed in Watts. This is the maximum chip internal power.

P_{I/O} max represents the maximum power dissipation on output pins where:

 $\mathsf{P}_{\mathsf{I}/\mathsf{O}} \max = \Sigma (\mathsf{V}_{\mathsf{OL}} \times \mathsf{I}_{\mathsf{OL}}) + \Sigma ((\mathsf{V}_{\mathsf{DD}} - \mathsf{V}_{\mathsf{OH}}) \times \mathsf{I}_{\mathsf{OH}}),$

taking into account the actual V_{OL} / I_{OL} and V_{OH} / I_{OH} of the I/Os at low and high level in the application.

Symbol	Parameter	Value	Unit
	Thermal resistance junction-ambient LQFP48 - 7 x 7 mm / 0.5 mm pitch	57	°C/W
	Thermal resistance junction-ambient LQFP32 - 7 x 7 mm / 0.8 mm pitch	60	
Θ _{JA}	Thermal resistance junction-ambient UFQFPN32 - 5 x 5 mm / 0.5 mm pitch	39	
	Thermal resistance junction-ambient UFQFPN28 - 4 x 4 mm / 0.5 mm pitch	120	
	Thermal resistance junction-ambient WLCSP25 - 0.4 mm pitch	70	
	Thermal resistance junction-ambient TSSOP20 - 169 mils	60	

Table	77.	Thermal	characte	eristics
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DocID027063 Rev 4

